



Shantou Huashan Electronic Devices Co.,Ltd.

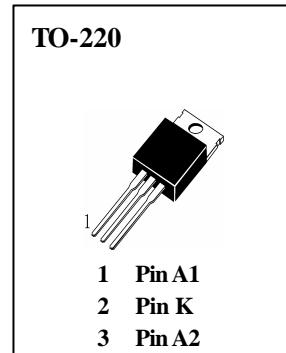
HJP1060CT

10A SCHOTTKY BARREIER RECTIFIER

Features

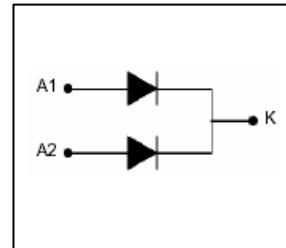
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheelings, and Polarity Protection Applications

Package



Maximum Ratings

■ T_{stg} —Storage Temperature.....	-55~150
■ T_j —Operating Temperature.....	125
■ V_{RRM} —Peak Repetitive Reverse Voltage.....	60V
■ V_{RWM} — Working Peak Reverse Voltage.....	60V
■ V_R —DC Blocking Voltage.....	60V
■ $V_{R(RMS)}$ — RMS Reverse Voltage.....	42V
■ $I_{F(AV)}$ —Average Rectified Output Current@ $T_c=95$	Double Dies 10A
◆ (Note 1)	Single Die 5A
■ I_{FSM} —Non-Repetitive Peak Forward Surge Current (Single Die , 60Hz)	125A



Electrical Characteristic@ $T_a=25$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	Min	Max	Unit	Condition
Forward Voltage Drop (Note 1)	V_{FM}		0.7	V	$I_F=5A, T_C=25$
Peak Reverse Current at Rated DC Blocking Voltage	I_{RM}		0.5 50	mA	$V_R = V_{RRM} \quad T_C=25$ $T_C=100$
Typical Junction Capacitance(Note 3)	C_J		250	pF	
Typical Thermal Resistance Junction to Case(Note 2)	R_{th-j}		3.0	/W	

Notes: 1、300μS Pulse Width, 2% Duty Cycle.

2、Thermal resistance junction to case mounted on heatsink.

3、Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V DC.



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PERFORMANCE CURVES

FIG.1 - FORWARD CURRENT DERATING CURVE

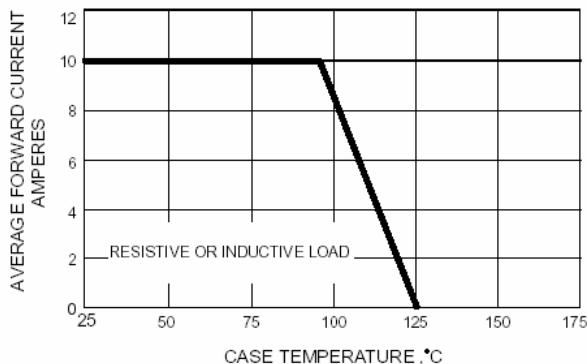


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

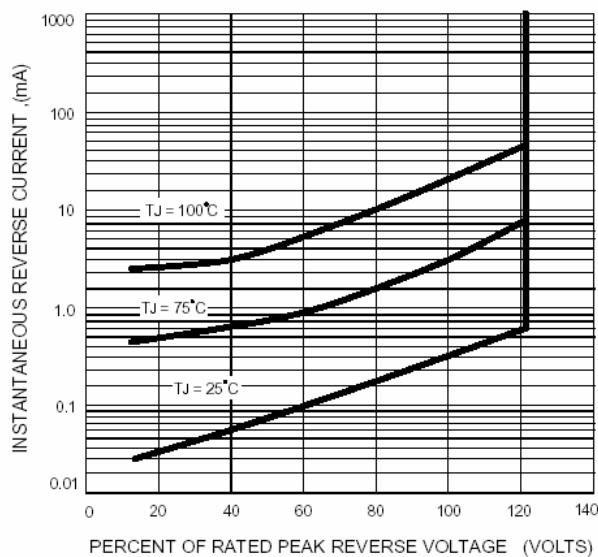


FIG.5 - TYPICAL JUNCTION CAPACITANCE

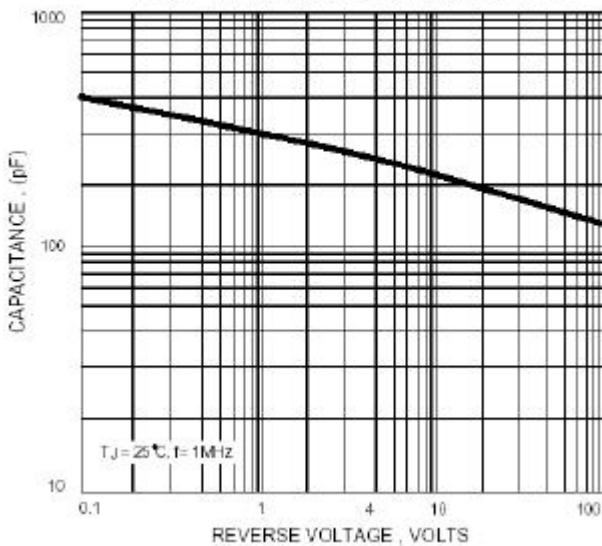


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

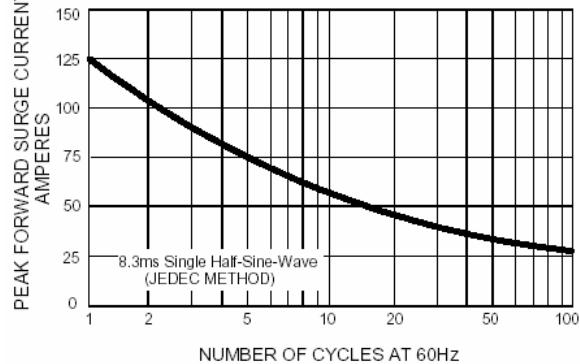


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

